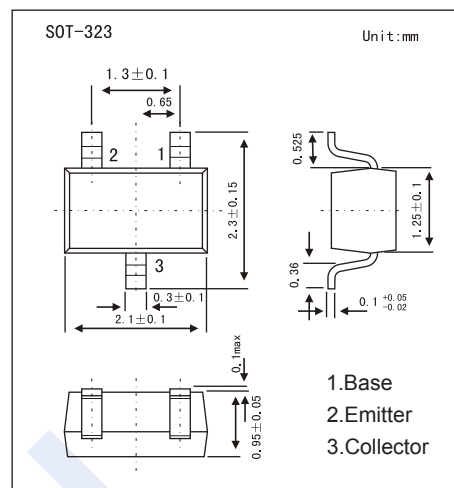


NPN Transistors

MMST2222A (KMST2222A)

■ Features

- Epitaxial planar die construction
- Complementary to MMST2907A



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	75	V
Collector - Emitter Voltage	V _{CEO}	40	
Emitter - Base Voltage	V _{EBO}	6	
Collector Current - Continuous	I _C	600	mA
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

NPN Transistors

MMST2222A (KMST2222A)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E = 0	75			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B = 0	40			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C = 0	6			
Collector-base cut-off current	I _{CBO}	V _{CB} = 75 V, I _E = 0			100	nA
Collector-emitter cut-off current	I _{CES}	V _{CE} = 35 V, I _B =0			100	
Emitter cut-off current	I _{EBO}	V _{EB} = 6 V, I _C =0			100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =150 mA, I _B =15mA			0.3	V
		I _C = 500 mA, I _B = 50mA			1	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =150 mA, I _B =15mA			1.2	
		I _C = 500 mA, I _B = 50mA			2	
DC current gain	h _{FE(1)}	V _{CE} = 10V, I _C = 0.1mA	35			
	h _{FE(2)}	V _{CE} = 10V, I _C = 1mA	50			
	h _{FE(3)}	V _{CE} = 10V, I _C = 10mA	75			
	h _{FE(4)}	V _{CE} = 10V, I _C = 150mA	100		300	
	h _{FE(5)}	V _{CE} = 10V, I _C = 500mA	40			
	h _{FE(6)}	V _{CE} = 1V, I _C = 150mA	35			
Delay time	t _d	V _{CC} =30V, V _{BE(off)} = -0.5V			10	nS
Rise time	t _r	I _C =150mA, I _{B1} =15mA			25	
Storage time	t _s	V _{CC} =30V, I _C =150mA, I _{B1} =-I _{B2} =15mA			225	
Fall time	t _f				60	
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz			8	pF
Transition frequency	f _T	V _{CE} = 20V, I _C = 20mA, f=100MHz	300			MHz

■ Marking

Marking	K3P
---------	-----